MICROCHIP

27C256

256K (32K x 8) CMOS EPROM

FEATURES

- High speed performance
  - 90 ns access time available
- CMOS Technology for low power consumption
  - 20 mA Active current
  - 100 µA Standby current
- Factory programming available
- Auto-insertion-compatible plastic packages
- Auto ID aids automated programming
- Separate chip enable and output enable controls
- High speed “express” programming algorithm
- Organized 32K x 8: JEDEC standard pinouts
  - 28-pin Dual-in-line package
  - 32-pin PLCC Package
  - 28-pin SOIC package
  - 28-pin Thin Small Outline Package (TSOP)
  - 28-pin Very Small Outline Package (VSOP)
  - Tape and reel
- Data Retention > 200 years
- Available for the following temperature ranges:
  - Commercial: 0˚C to +70˚C
  - Industrial: -40˚C to +85˚C
  - Automotive: -40˚C to +125˚C

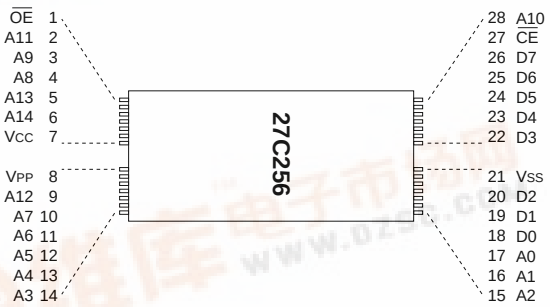
DESCRIPTION

The Microchip Technology Inc. 27C256 is a CMOS 256K bit electrically Programmable Read Only Memory (EPROM). The device is organized as 32K words by 8 bits (32K bytes). Accessing individual bytes from an address transition or from power-up (chip enable pin going low) is accomplished in less than 90 ns. This very high speed device allows the most sophisticated microprocessors to run at full speed without the need for WAIT states. CMOS design and processing enables this part to be used in systems where reduced power consumption and reliability are requirements.

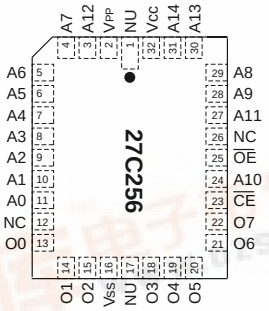
A complete family of packages is offered to provide the most flexibility in applications. For surface mount applications, PLCC, SOIC, VSOP or TSOP packaging is available. Tape and reel packaging is also available for PLCC or SOIC packages.

PACKAGE TYPES

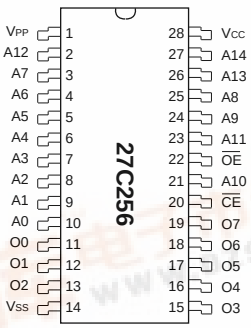
TSOP



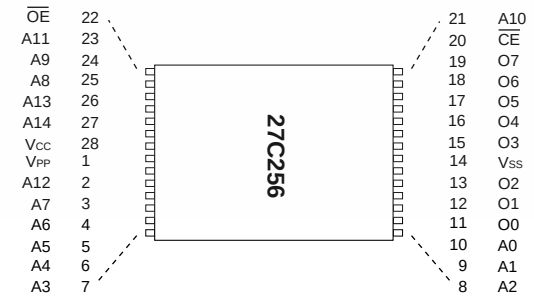
PLCC



DIP/SOIC



VSOP



1.0 ELECTRICAL CHARACTERISTICS

1.1 Maximum Ratings*

V_{CC} and input voltages w.r.t. V_{SS} ..... -0.6V to +7.25V

V_{PP} voltage w.r.t. V_{SS} during programming ..... -0.6V to +14.0V

Voltage on A9 w.r.t. V_{SS} ..... -0.6V to +13.5V

Output voltage w.r.t. V_{SS} ..... -0.6V to V_{CC} +1.0V

Storage temperature ..... -65˚C to +150˚C

Ambient temp. with power applied ..... -65˚C to +125˚C

*Notice: Stresses above those listed under “Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

TABLE 1-1: PIN FUNCTION TABLE

Name	Function
A0-A14	Address Inputs
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
V_{PP}	Programming Voltage
O0 - O7	Data Output
V_{CC}	+5V Power Supply
V_{SS}	Ground
NC	No Connection; No Internal Connection
NU	Not Used; No External Connection Is Allowed

TABLE 1-2: READ OPERATION DC CHARACTERISTICS

V_{CC} = +5V (±10%)
Commercial: Tamb = 0˚C to +70˚C
Industrial: Tamb = -40˚C to +85˚C
Extended (Automotive): Tamb = -40°C to +125°C

Parameter	Part*	Status	Symbol	Min.	Max.	Units	Conditions
Input Voltages	all	Logic "1" Logic "0"	V_{IH} V_{IL}	2.0 -0.5	V_{CC}+1 0.8	V V	
Input Leakage	all	—	I_{LI}	-10	10	µA	V_{IN} = 0 to V_{CC}
Output Voltages	all	Logic "1" Logic "0"	V_{OH} V_{OL}	2.4	 0.45	V V	I_{OH} = -400 µA I_{OL} = 2.1 mA
Output Leakage	all	—	I_{LO}	-10	10	µA	V_{OUT} = 0V to V_{CC}
Input Capacitance	all	—	C_{IN}	—	6	pF	V_{IN} = 0V; Tamb = 25°C; f = 1 MHz
Output Capacitance	all	—	C_{OUT}	—	12	pF	V_{OUT} = 0V; Tamb = 25°C; f = 1 MHz
Power Supply Current, Active	C I,E	TTL input TTL input	I_{CC1} I_{CC2}	— —	20 25	mA mA	V_{CC} = 5.5V; V_{PP} = V_{CC} f = 1 MHz; $\overline{OE}$ = $\overline{CE}$ = V_{IL}; I_{OUT} = 0 mA; V_{IL} = -0.1 to 0.8V; V_{IH} = 2.0 to V_{CC}; Note 1
Power Supply Current, Standby	C I, E all	TTL input TTL input CMOS input	$I_{CC(S)}$	—	2 3 100	mA mA µA	 $\overline{CE}$ = V_{CC} ± 0.2V
I_{PP} Read Current V_{PP} Read Voltage	all all	Read Mode Read Mode	I_{PP} V_{PP}	 V_{CC}-0.7	100 V_{CC}	µA V	V_{PP} = 5.5V

* Parts: C=Commercial Temperature Range; I, E=Industrial and Extended Temperature Ranges

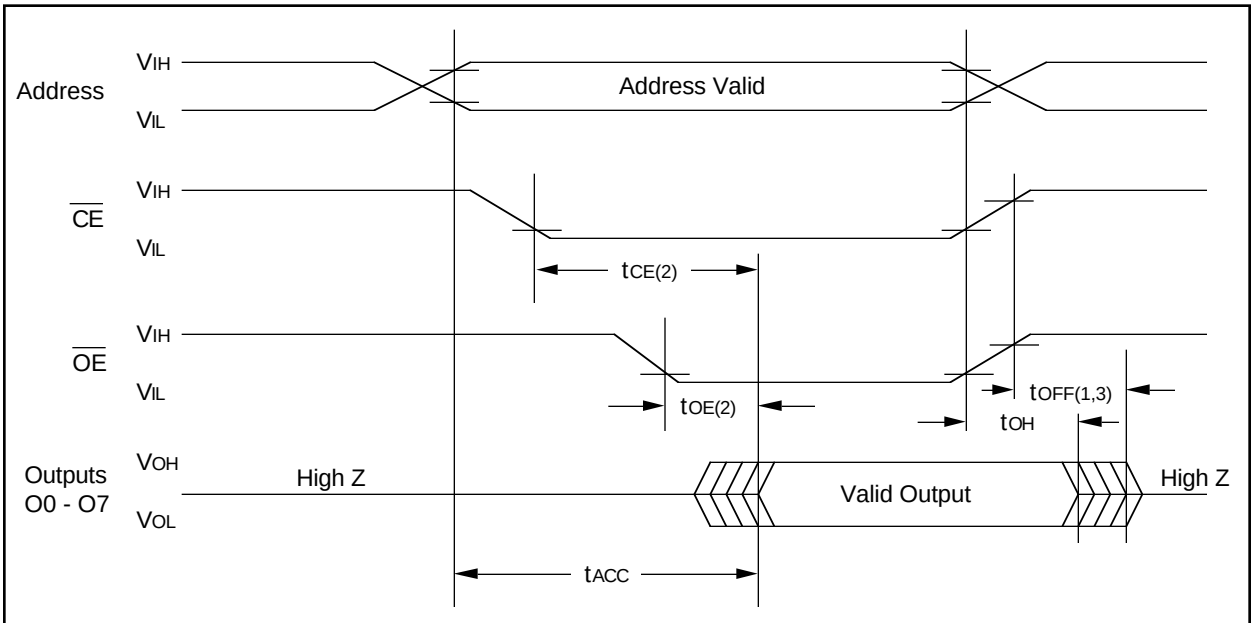
Note 1: Typical active current increases .75 mA per MHz up to operating frequency for all temperature ranges.

TABLE 1-3: READ OPERATION AC CHARACTERISTICS

AC Testing Waveform: V_{IH} = 2.4V and V_{IL} = 0.45V; V_{OH} = 2.0V V_{OL} = 0.8V Output Load: 1 TTL Load + 100 pF Input Rise and Fall Times: 10 ns Ambient Temperature: Commercial: Tamb = 0°C to +70°C Industrial: Tamb = -40°C to +85°C Automotive: Tamb = -40°C to +125°C													
Parameter	**Sym**	**27C256-90***		**27C256-10***		**27C256-12**		**27C256-15**		**27C256-20**		**Units**	**Conditions**
		Min	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**		
Address to Output Delay	t_{ACC}	—	90	—	100	—	120	—	150	—	200	ns	$\overline{CE}$=$\overline{OE}$ =V_{IL}
$\overline{CE}$ to Output Delay	t_{CE}	—	90	—	100	—	120	—	150	—	200	ns	$\overline{OE}$ = V_{IL}
$\overline{OE}$ to Output Delay	t_{OE}	—	40	—	45	—	55	—	65	—	75	ns	$\overline{CE}$ = V_{IL}
$\overline{CE}$ or $\overline{OE}$ to O/P High Impedance	t_{OFF}	0	30	0	30	0	35	0	50	0	55	ns	
Output Hold from Address $\overline{CE}$ or $\overline{OE}$, whichever goes first	t_{OH}	0	—	0	—	0	—	0	—	0	—	ns	

* -10, -90 AC Testing Waveform: V_{IH} = 2.4V and V_{IL} = .45V; V_{OH} = 1.5V and V_{OL} = 1.5V
Output Load: 1 TTL Load + 30pF

FIGURE 1-1: READ WAVEFORMS



Notes: (1) t_{OFF} is specified for $\overline{OE}$ or $\overline{CE}$, whichever occurs first
(2) $\overline{OE}$ may be delayed up to t_{CE} - t_{OE} after the falling edge of $\overline{CE}$ without impact on t_{CE}
(3) This parameter is sampled and is not 100% tested.

TABLE 1-4: PROGRAMMING DC CHARACTERISTICS

			Ambient Temperature: Tamb = 25°C ± 5°C V_{CC} = 6.5V ± 0.25V, V_{PP} = V_H = 13.0V ± 0.25V			
Parameter	**Status**	**Symbol**	**Min**	**Max.**	**Units**	**Conditions**
Input Voltages	Logic"1" Logic"0"	V_{IH} V_{IL}	2.0 -0.1	V_{CC}+1 0.8	V V	
Input Leakage	—	I_{LI}	-10	10	µA	V_{IN} = 0V to V_{CC}
Output Voltages	Logic"1" Logic"0"	V_{OH} V_{OL}	2.4	 0.45	V V	I_{OH} = -400 µA I_{OL} = 2.1 mA
V_{CC} Current, program & verify	—	I_{CC2}	—	20	mA	Note 1
V_{PP} Current, program	—	I_{PP2}	—	25	mA	Note 1
A9 Product Identification	—	V_H	11.5	12.5	V	

Note 1: V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}

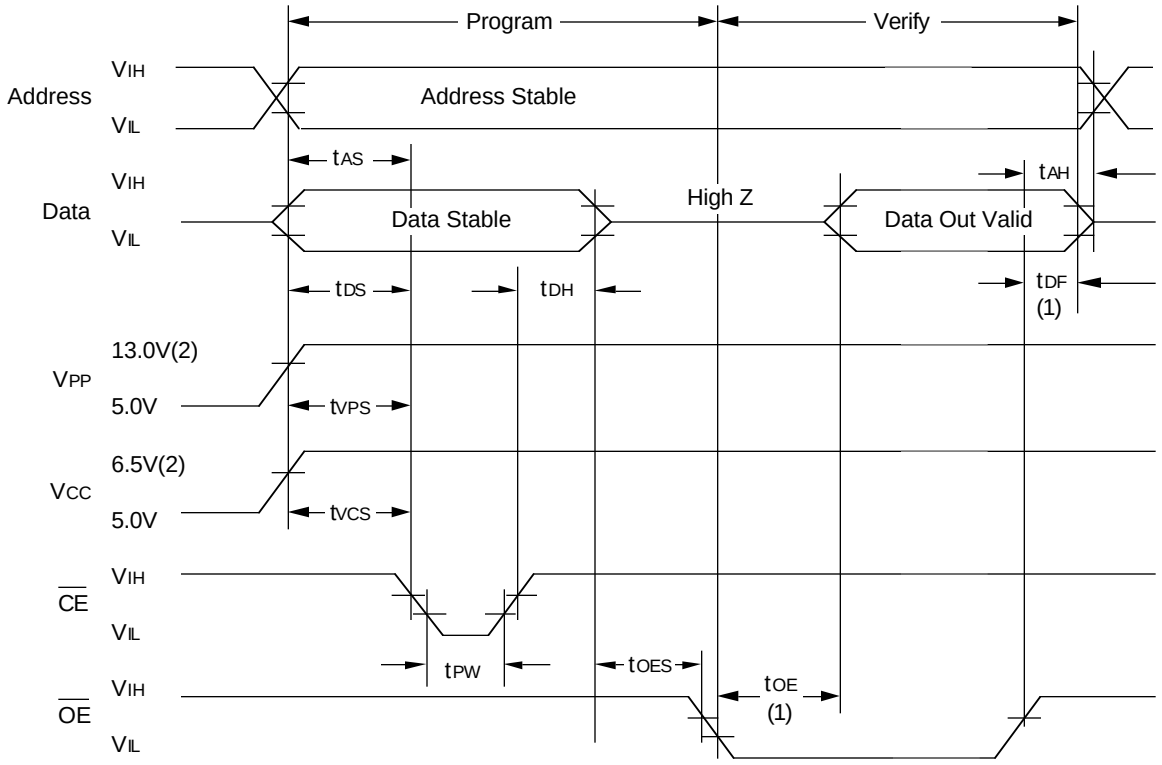
TABLE 1-5: PROGRAMMING AC CHARACTERISTICS

for Program, Program Verify and Program Inhibit Modes	AC Testing Waveform: V_{IH}=2.4V and V_{IL}=0.45V; V_{OH}=2.0V; V_{OL}=0.8V Output Load: 1 TTL Load + 100pF Ambient Temperature: Tamb=25°C ± 5°C V_{CC}= 6.5V ± 0.25V, V_{PP} = V_H = 13.0V ± 0.25V				
Parameter	**Symbol**	**Min.**	**Max.**	**Units**	**Remarks**
Address Set-Up Time	t_{AS}	2	—	µs	
Data Set-Up Time	t_{DS}	2	—	µs	
Data Hold Time	t_{DH}	2	—	µs	
Address Hold Time	t_{AH}	0	—	µs	
Float Delay (2)	t_{DF}	0	130	ns	
V_{CC} Set-Up Time	t_{VCS}	2	—	µs	
Program Pulse Width (1)	t_{PW}	95	105	µs	100 µs typical
$\overline{CE}$ Set-Up Time	t_{CES}	2	—	µs	
$\overline{OE}$ Set-Up Time	t_{OES}	2	—	µs	
V_{PP} Set-Up Time	t_{VPS}	2	—	µs	
Data Valid from $\overline{OE}$	t_{OE}	—	100	ns	

Note 1: For express algorithm, initial programming width tolerance is 100 µs ±5%.

2: This parameter is only sampled and not 100% tested. Output float is defined as the point where data is no longer driven (see timing diagram).

FIGURE 1-2: PROGRAMMING WAVEFORMS



Notes: (1) t_{DF} and t_{OE} are characteristics of the device but must be accommodated by the programmer
(2) V_{CC} = 6.5 V ±0.25V, V_{PP} = V_H = 13.0V ±0.25V for express algorithm

TABLE 1-6: MODES

Operation Mode	$\overline{CE}$	OE	V_{PP}	A9	O0 - O7
Read	V_{IL}	V_{IL}	V_{CC}	X	D_{OUT}
Program	V_{IL}	V_{IH}	V_H	X	D_{IN}
Program Verify	V_{IH}	V_{IL}	V_H	X	D_{OUT}
Program Inhibit	V_{IH}	V_{IH}	V_H	X	High Z
Standby	V_{IH}	X	V_{CC}	X	High Z
Output Disable	V_{IL}	V_{IH}	V_{CC}	X	High Z
Identity	V_{IL}	V_{IL}	V_{CC}	V_H	Identity Code

X = Don't Care

1.2 Read Mode

(See Timing Diagrams and AC Characteristics)

Read Mode is accessed when:

a) the $\overline{CE}$ pin is low to power up (enable) the chip
b) the $\overline{OE}$ pin is low to gate the data to the output pins

For Read operations, if the addresses are stable, the address access time (t_{ACC}) is equal to the delay from $\overline{CE}$ to output (t_{CE}). Data is transferred to the output after a delay from the falling edge of $\overline{OE}$ (t_{OE}).

1.3 Standby Mode

The standby mode is defined when the $\overline{CE}$ pin is high (VIH) and a program mode is not defined.

When these conditions are met, the supply current will drop from 20 mA to 100 μA.

1.4 Output Enable

This feature eliminates bus contention in multiple bus microprocessor systems and the outputs go to a high impedance when the following condition is true:

- The $\overline{OE}$ pin is high and the program mode is not defined.

1.5 Erase Mode (U.V. Windowed Versions)

Windowed products offer the ability to erase the memory array. The memory matrix is erased to the all 1's state when exposed to ultraviolet light. To ensure complete erasure, a dose of 15 watt-second/cm^2 is required. This means that the device window must be placed within one inch and directly underneath an ultraviolet lamp with a wavelength of 2537 Angstroms, intensity of 12,000μW/cm^2 for approximately 20 minutes.

1.6 Programming Mode

The Express Algorithm has been developed to improve on the programming throughput times in a production environment. Up to ten 100-microsecond pulses are applied until the byte is verified. No overprogramming is required. A flowchart of the express algorithm is shown in Figure 1-3.

Programming takes place when:

a) V_{CC} is brought to the proper voltage,
b) V_{PP} is brought to the proper V_H level,
c) the $\overline{OE}$ pin is high, and
d) the $\overline{CE}$ pin is low.

Since the erased state is "1" in the array, programming of "0" is required. The address to be programmed is set via pins A0-A14 and the data to be programmed is presented to pins O0-O7. When data and address are stable, a low going pulse on the $\overline{CE}$ line programs that location.

1.7 Verify

After the array has been programmed it must be verified to ensure all the bits have been correctly programmed. This mode is entered when all the following conditions are met:

a) V_{CC} is at the proper level,
b) V_{PP} is at the proper V_H level,
c) the $\overline{CE}$ line is high, and
d) the $\overline{OE}$ line is low.

1.8 Inhibit

When programming multiple devices in parallel with different data, only $\overline{CE}$ need be under separate control to each device. By pulsing the $\overline{CE}$ line low on a particular device, that device will be programmed; all other devices with $\overline{CE}$ held high will not be programmed with the data, although address and data will be available on their input pins.

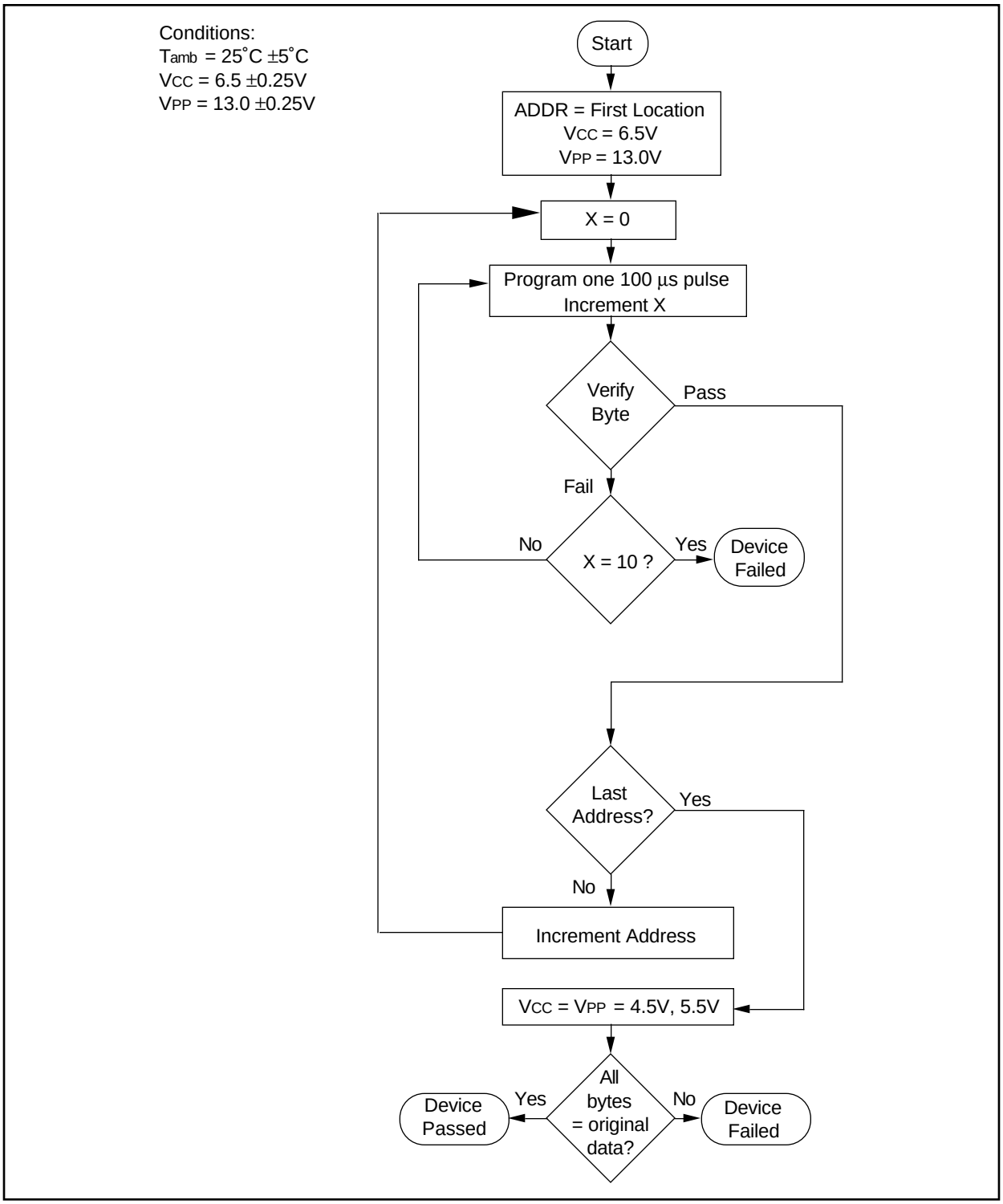
1.9 Identity Mode

In this mode specific data is output which identifies the manufacturer as Microchip Technology Inc. and device type. This mode is entered when Pin A9 is taken to V_H (11.5V to 12.5V). The $\overline{CE}$ and $\overline{OE}$ lines must be at V_{IL}. A0 is used to access any of the two non-erasable bytes whose data appears on O0 through O7.

Pin →	Input	Output								
Identity ↓	A0	O7	O6	O5	O4	O3	O2	O1	O0	Hex
Manufacturer	V_{IL}	0	0	1	0	1	0	0	1	29
Device Type*	V_{IH}	1	0	0	0	1	1	0	0	8C

* Code subject to change

FIGURE 1-3: PROGRAMMING EXPRESS ALGORITHM



NOTES:

NOTES:

NOTES:

27C256 Product Identification System

To order or to obtain information (e.g., on pricing or delivery), please use listed part numbers, and refer to factory or listed sales offices.

27C256 – 90 I /TS

Package:	L	=	Plastic Leaded Chip Carrier
	P	=	Plastic DIP (Mil 600)
	SO	=	Plastic SOIC (Mil 300)
	TS	=	Thin Small Outline Package (TSOP) 8x20mm
	VS	=	Very Small Outline Package (VSOP) 8x13.4mm
Temperature Range:	Blank	=	0˚C to +70˚C
	I	=	-40˚C to +85˚C
	E	=	-40˚C to +125˚C
Access Time:	90	=	90 ns
	10	=	100 ns
	12	=	120 ns
	15	=	150 ns
	20	=	200 ns
Device	27C256		256K (32K x 8) CMOS EPROM

WORLDWIDE SALES & SERVICE

AMERICAS

Corporate Office
Microchip Technology Inc.
2355 West Chandler Blvd.
Chandler, AZ 85224-6199
Tel: 602 786-7200 Fax: 602 786-7277
Technical Support: 602 786-7627
Web: http://www.microchip.com

Atlanta
Microchip Technology Inc.
500 Sugar Mill Road, Suite 200B
Atlanta, GA 30350
Tel: 770 640-0034 Fax: 770 640-0307

Boston
Microchip Technology Inc.
5 Mount Royal Avenue
Marlborough, MA 01752
Tel: 508 480-9990 Fax: 508 480-8575

Chicago
Microchip Technology Inc.
333 Pierce Road, Suite 180
Itasca, IL 60143
Tel: 708 285-0071 Fax: 708 285-0075

Dallas
Microchip Technology Inc.
14651 Dallas Parkway, Suite 816
Dallas, TX 75240-8809
Tel: 972 991-7177 Fax: 972 991-8588

Dayton
Microchip Technology Inc.
Suite 150
Two Prestige Place
Miamisburg, OH 45342
Tel: 513 291-1654 Fax: 513 291-9175

Los Angeles
Microchip Technology Inc.
18201 Von Karman, Suite 1090
Irvine, CA 92612
Tel: 714 263-1888 Fax: 714 263-1338

New York
Microchip Technmgy Inc.
150 Motor Parkway, Suite 416
Hauppauge, NY 11788
Tel: 516 273-5305 Fax: 516 273-5335

San Jose
Microchip Technology Inc.
2107 North First Street, Suite 590
San Jose, CA 95131
Tel: 408 436-7950 Fax: 408 436-7955

Toronto
Microchip Technology Inc.
5925 Airport Road, Suite 200
Mississauga, Ontario L4V 1W1, Canada
Tel: 905 405-6279 Fax: 905 405-6253

ASIA/PACIFIC

China
Microchip Technology
Unit 406 of Shanghai Golden Bridge Bldg.
2077 Yan'an Road West, Hongiao District
Shanghai, Peoples Republic of China
Tel: 86 21 6275 5700
Fax: 011 86 21 6275 5060

Hong Kong
Microchip Technology
RM 3801B, Tower Two
Metroplaza
223 Hing Fong Road
Kwai Fong, N.T. Hong Kong
Tel: 852 2 401 1200 Fax: 852 2 401 3431

India
Microchip Technology
No. 6, Legacy, Convent Road
Bangalore 560 025 India
Tel: 91 80 526 3148 Fax: 91 80 559 9840

Korea
Microchip Technology
168-1, Youngbo Bldg. 3 Floor
Samsung-Dong, Kangnam-Ku,
Seoul, Korea
Tel: 82 2 554 7200 Fax: 82 2 558 5934

Singapore
Microchip Technology
200 Middle Road
#10-03 Prime Centre
Singapore 188980
Tel: 65 334 8870 Fax: 65 334 8850

Taiwan, R.O.C
Microchip Technology
10F-1C 207
Tung Hua North Road
Taipei, Taiwan, ROC
Tel: 886 2 717 7175 Fax: 886 2 545 0139

EUROPE

United Kingdom
Arizona Microchip Technology Ltd.
Unit 6, The Courtyard
Meadow Bank, Furlong Road
Bourne End, Buckinghamshire SL8 5AJ
Tel: 44 1628 850303 Fax: 44 1628 850178

France
Arizona Microchip Technology SARL
Zone Industrielle de la Bonde
2 Rue du Buisson aux Fraises
91300 Massy - France
Tel: 33 1 69 53 63 20 Fax: 33 1 69 30 90 79

Germany
Arizona Microchip Technology GmbH
Gustav-Heinemann-Ring 125
D-81739 Muenchen, Germany
Tel: 49 89 627 144 0 Fax: 49 89 627 144 44

Italy
Arizona Microchip Technology SRL
Centro Direzionale Colleone Pas Taurus 1
Viale Colleoni 1
20041 Agrate Brianza
Milan Italy
Tel: 39 39 6899939 Fax: 39 39 689 9883

JAPAN

Microchip Technology Intl. Inc.
Benex S-1 6F
3-18-20, Shin Yokohama
Kohoku-Ku, Yokohama
Kanagawa 222 Japan
Tel: 81 45 471 6166 Fax: 81 45 471 6122

9/3/96

MICROCHIP

Printed on recycled paper.